



Docket: T00-338  
S/N 09/785,114

### Amendment

In response to the above mentioned Office action please amend the spec and claims as follows:

#### CLEAN VERSION

#### In the Specification

##### In the specification

Please replace the 1st full Paragraph on spec p. 10 with the following rewritten paragraph:

a<sup>1</sup>  
In a critical step in the invention, as shown in FIG 3, we form a mask (e.g., resist) pattern 56 over the cell node 40. Any implant blocking mask can be used. This resist pattern serves to block a subsequent high concentration (e.g., P+) implant into the node cell region.

Please replace the 2nd full Paragraph on spec p. 12 with the following rewritten paragraph:

a<sup>2</sup>  
The bit line region 34 60 consists of a first bit line region 34 and a second bit line region 60. The first bit line region 34 has about the same impurity concentration as the cell node 40.

##### In the Claims

Please amend the claims as follows:

1.(AMENDED) A method of fabrication of a 1T Static Random Access Memory (SRAM), comprising the steps of:

- a<sup>3</sup>  
a) forming a word line structure and a capacitor plate structure on a substrate;
- (1) said capacitor plate structure comprised of a capacitor dielectric on said substrate and a conductive plate layer on said capacitor dielectric; said

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